

Silicon PNP Power Transistor

2SB1566

DESCRIPTION

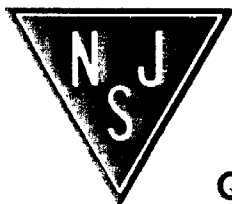
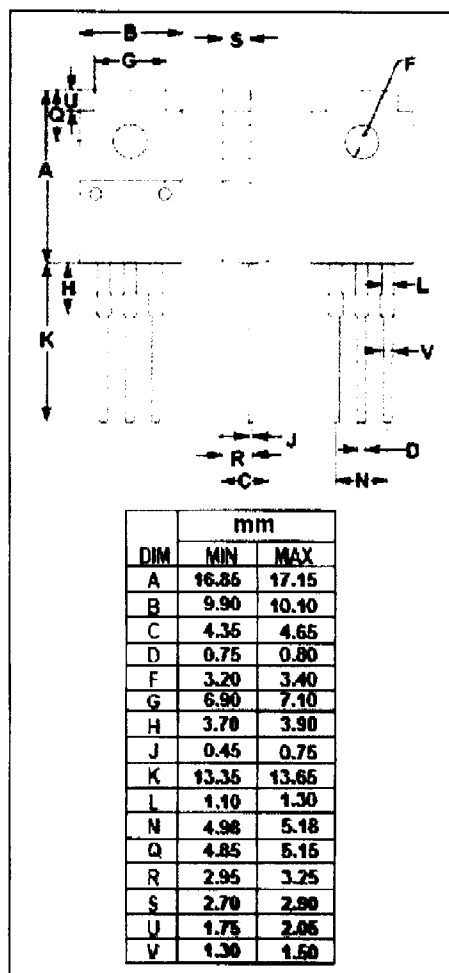
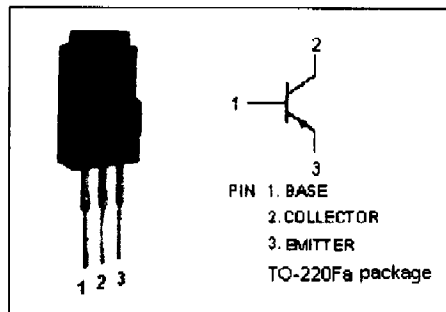
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -50V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -1.0V(\text{Max}) @ (I_C = -2A, I_B = -0.2A)$
- Wide Area of Safe Operation
- Complement to Type 2SD2395

APPLICATIONS

- Designed for power amplifications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-4.5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; I _B = 0	-50			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -50 μ A; I _E = 0	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -50 μ A; I _C = 0	-7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.5A; V _{CE} = -3V	100		320	
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -5V; f _{test} = 5MHz		60		MHz
C _{OB}	Collector Output Capacitance	I _E = 0; V _{CE} = -10V; f _{test} = 1MHz		40		pF

◆ h_{FE} Classifications

E	F
100-200	160-320